

4V Drive Nch MOSFET

RP1E070XN

Structure

Silicon N-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (MPT6).

Application

Switching

Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	1000	
RP1E070X	0		

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±7	Α
	Pulsed	I _{DP} *1	±18	Α
Source current	Continuous	l _s	1.6	Α
(Body Diode)	Pulsed	I _{SP} *1	18	Α
Power dissipation		P _D *2	2.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

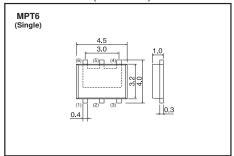
^{*1} Pw≤10μs, Duty cycle≤1%

• Thermal resistance

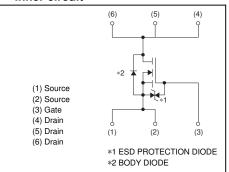
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	62.5	°C/W

^{*}Mounted on a ceramic board.

● Dimensions (Unit : mm)



• Inner circuit



^{*2} Mounted on a ceramic board.

• Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	1	-	±10	μA	$V_{GS}=\pm20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	1	-	1	μA	V_{DS} =30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	1	2.5	٧	$V_{DS}=10V$, $I_{D}=1mA$
Static dualing accuracy are state	*	1	20	28		$I_D=7A$, $V_{GS}=10V$
Static drain-source on-state resistance	R _{DS (on)}	-	25	35	mΩ	$I_{D}=7A, V_{GS}=4.5V$
		1	28	39		$I_{D}=7A, V_{GS}=4.0V$
Forward transfer admittance	I Y _{fs} ľ	4.5	-	-	S	$I_D=7A$, $V_{DS}=10V$
Input capacitance	C _{iss}	1	390	-	рF	V _{DS} =10V
Output capacitance	C _{oss}	1	150	-	рF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	70	-	рF	f=1MHz
Turn-on delay time	t _{d(on)} *	1	7	-	ns	I _D =3.5A, V _{DD} ≒15V
Rise time	t _r *	-	30	-	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	1	30	-	ns	$R_L=4.3\Omega$
Fall time	t _f *	1	8	-	ns	$R_G=10\Omega$
Total gate charge	Q _g *	-	5.8	-	nC	I _D =7A, V _{DD} ≒ 15V
Gate-source charge	Q _{gs} *	-	1.5	-	nC	$V_{GS}=5V$
Gate-drain charge	Q _{gd} *	-	2.3	-	nC	

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	1.2	V	I _s =7A, V _{GS} =0V

^{*}Pulsed

2/6

●Electrical characteristic curves (Ta=25°C)

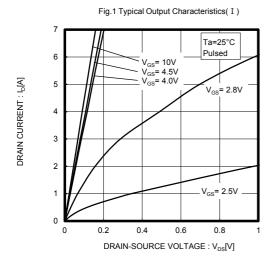


Fig.3 Typical Transfer Characteristics

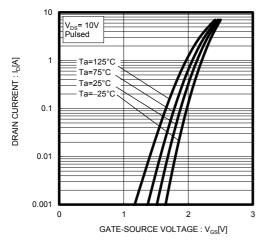


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

1000

Vos=10V

Pulsed

Ta=125°C

Ta=75°C

Ta=25°C

Ta=25°C

Ta=25°C

Ta=-25°C

Ta=-25°C

Ta=25°C Pulsed

V_{GS}= 4.5V

V_{GS}= 4.0V

V_{GS}= 2.5V

V_{GS}= 2.5V

0

0

Fig.2 Typical Output Characteristics(II)

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DRAIN-SOURCE VOLTAGE : $V_{DS}[V]$

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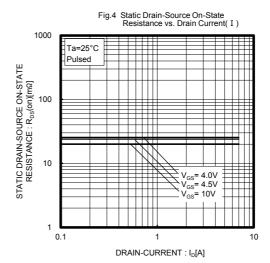
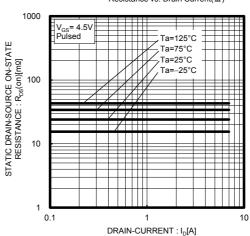
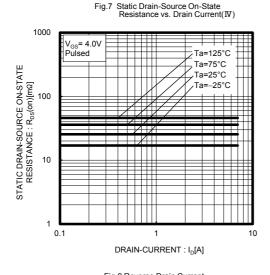
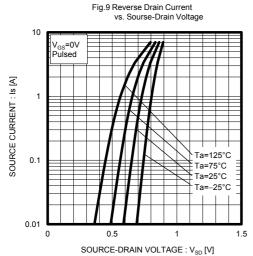
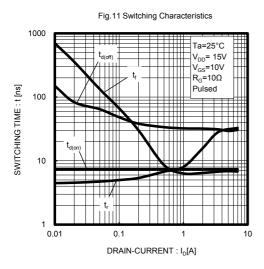


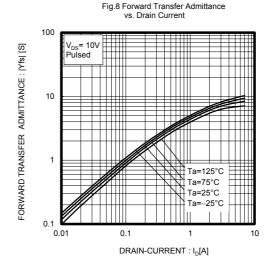
Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

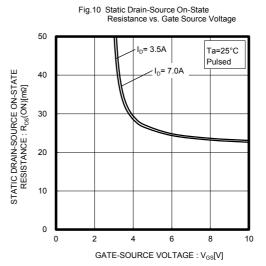


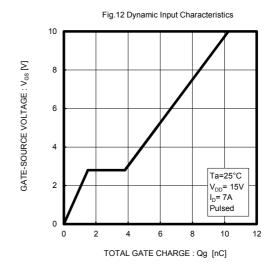












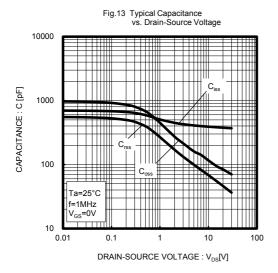
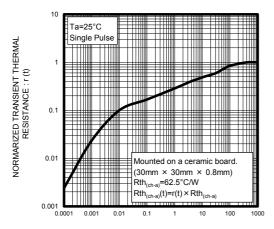
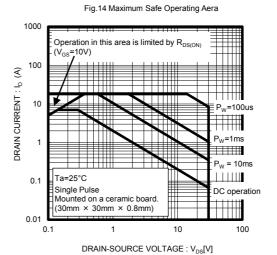


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width



PULSE WIDTH : Pw(s)



Measurement circuits

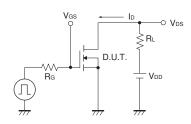


Fig.1-1 Switching Time Measurement Circuit

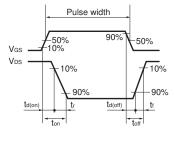


Fig.1-2 Switching Waveforms

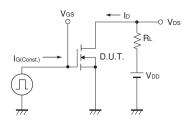


Fig.2-1 Gate Charge Measurement Circuit

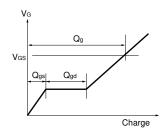


Fig.2-2 Gate Charge Waveform

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

6/6

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